

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. ASMEX.186DV1	APPLICATION NO. Unknown <i>09,764,711</i>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Raaijmakers et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	3,900,597	08/19/75	Chruma et al.			
	4,062,707	12/13/77	Mochizuki et al.			
	4,217,374	08/12/80	Ovshinsky et al.			
	4,237,150	12/02/80	Wiesmann			
	4,341,818	07/27/82	Adams et al.			
	4,379,020	04/05/83	Glaeser et al.			
	4,404,236	09/13/83	Komatsu et al.			
	4,444,812	04/24/84	Gutsche			
	4,466,922	08/21/84	Weitz et al.			
	4,592,933	06/03/86	Meyerson et al.			
	4,634,605	01/06/87	Wiesmann			
	4,745,088	05/17/88	Inoue et al.			
	4,843,022	06/27/89	Yamazaki			
	4,963,506	10/16/90	Liaw et al.			
	5,017,308	05/21/91	Iijima et al.			
	5,037,666	08/06/91	Mori			
	5,080,933	01/14/92	Grupen-Shemansky et al.			
	5,075,749	12/24/91	Chi et al.			
	5,082,696	01/21/92	Sharp			
	5,198,387	3/99	Tang			
	5,254,369	10/19/93	Arai et al.			
	5,314,845	05/24/94	Lee et al.			
	5,324,684	6/94	Kermani et al.			
	5,576,059	11/19/96	Beinglass et al.			
	5,593,727	01/14/97	Desu et al.			
	5,607,511	3/4/97	Meyerson			
	5,607,724	03/04/97	Beinglass et al.			
	5,614,257	03/25/97	Beinglass et al.			
	5,695,819	12/09/97	Beinglass et al.			
	5,700,520	12/23/97	Beinglass et al.			
	5,863,598	01/26/99	Venkatesan et al.			04/12/96

12/10/96

10/08/97

AK	5,874,129	02/23/99	Beinglass et al.			
AN	5,876,797	03/02/99	Beinglass et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
AK	51-1389 ✓	1976	Japan			Yes	
AK	54-4066 ✓	1979	Japan			Yes	
AK	60-36662 ✓	1985	Japan			Yes	
AK	63-3414 ✓	1986	Japan			Yes	
AK	63-239811 ✓		Japan			Yes	
AK	63-258016 ✓		Japan			Yes	
AK	2-119223 ✓	1990	Japan			Yes	
AK	2-122076 ✓	1990	Japan			Yes	
AK	2-208293 ✓		Japan			Yes	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
AK	✓ Bloem, J. "High Chemical Vapour Deposition Rates of Epitaxial Silicon Layers", J. of Crystal Growth, Vol. 18, 1973, pp. 70-76. ✓
	✓ Bunshah et al. "Deposition Technologies for Films and Coatings; Developments and Applications," Noyes Publications, 1982, p. 357. ✓
	✓ Claasen et al., "The Deposition Of Silicon From Silane In a Low-Pressure Hot-Wall System", J. of Crystal Growth, Vol. 57, 1982, pp. 259-266. ✓
AK	✓ Kern, Werner. "Advances in Deposition Processes for Passivation films", J. Vac. Sci. Technol., Vol. 14, No. 5, 1977, pp. 1082-1099. ✓
	✓ Morosanu, C.E. Thin Films by Chemical Vapor Deposition, Elsevier, 1990, p. 48, 107. ✓
AK	✓ Schuegraf, K.K. Handbook of Thin-Film Deposition Processes And Techniques; Noyes Publications, 1988, pp. 80-81, 86, 93. ✓
	✓ C.R. Kleijn, "A Mathematical Model of the Hydrodynamics and Gas-Phase Reactions in Silicon LPCVD in a Single-Wafer Reactor," J. Electrochem Soc., Vol 138, No. 7, July 1991, pp. 1190-1200.

EXAMINER		DATE CONSIDERED	12/3/01
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			